In the Claims:

All pending claims are presented below for the convenience of the Examiner.

31. (Previously presented) A gate electrode comprising:

an insulative layer disposed on a substrate;

a gate layer disposed on said insulative layer, the gate layer being of uniform width

along a height thereof;

thin first spacers disposed adjacent to opposite sides of said gate layer;

thin second spacers disposed adjacent to opposite sides of said thin first spacers;

thin third spacers disposed adjacent to opposite sides of said thin second spacers;

thick fourth spacers disposed adjacent to opposite sides of said thin third spacers;

and

a conductive layer disposed on said gate layer, wherein at least part of the

conductive layer is wider than said gate layer.

123. (Previously presented) The gate electrode of claim 31, wherein the conductive layer

has a non-uniform cross-section defined by a narrower base section which is in contact

with the gate layer, and a wider top section.

124. (Previously presented) The gate electrode of claim 123, wherein the thin first

spacers and the thin second spacers are deformed to accommodate the wider top section

- 2 -

of the conductive layer.

Chia-Hong Jan

Application No.: 09/477,870

Examiner: Douglas Owens

Art Unit: 2811

125. (Previously presented) The gate electrode of claim 123, wherein the part of the conductive layer that is wider than the gate layer rests on at least the first thin spacer.

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126. (Previously presented) The gate electrode of claim 31 wherein said insulative layer comprises an oxide.

127. (Previously presented) The gate electrode of claim 126 wherein said gate layer comprises a polysilicon.

128. (Previously presented) The gate electrode of claim 127 wherein said conductive layer comprises a polycide.

129. (Previously presented) The gate electrode of claim 128 wherein said thin first spacers comprise an oxide.

130. (Previously presented) The gate electrode of claim 129 wherein said thin second spacers comprise a nitride.

131. (Previously presented) The gate electrode of claim 130 wherein said thin third spacers comprise an oxide.

Chia-Hong Jan - 3 - Examiner: Douglas Owens

Application No.: 09/477,870 Art Unit: 2811